

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph beginning on page 15, line 11 with the following:

[0040] An Over Etch (OE) step after the Main Etch (ME) may affect the composition of the chamber deposits. Table 3 shows the recipes used to study the effects of the OE step. The ME may include $C_xH_yF_z$ $C_xF_yH_z$ as a component wherein $x \geq 1$, $y \geq 1$, and $z \geq 0$. An example of representative gas is CHF_3 . The OE may be carried out with a $C_xH_yF_z$ -free $C_xF_yH_z$ -free gas, e.g., BCl_3 and/or Cl_2 as components. The wafers used were 50% Open Area Aluminum wafers (10,000 Å A1).

Please replace the paragraph beginning on page 16, line 2 with the following:

[0042] Figure 4 shows that when the base WAC was added after each wafer was processed with ME and OE, almost all of the deposit is eliminated. The amount of Al and F in the chamber deposit is surprisingly decreased with the addition of the $C_xH_yF_z$ -free $C_xF_yH_z$ -free OE step even without WAC. The OE step may eliminate the Al and F in the deposit, leaving mostly volatile substance. This was observed at all three test piece locations and suggests that the ME and OE process is efficient at removing both Al and F deposits and volatile matter.